



**MMDT5451Q** 

#### NPN / PNP SMALL SIGNAL TRANSISTOR IN SOT363

### Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

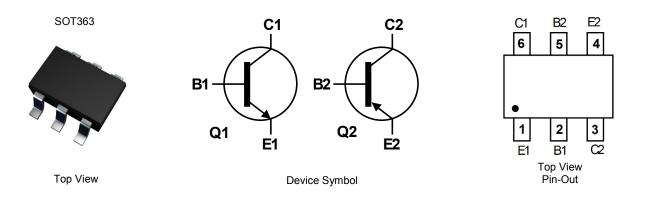
## Features

- Epitaxial Planar Die Construction
- Complementary Pair
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The MMDT5451Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

#### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Finish. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)



### Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
MMDT5451Q-7	AEC-Q101	KNM	7	8	3,000

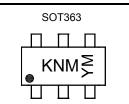
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



KNM = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

2029

R

Sep

9

2030

S

Oct

0

2031

T Nov

Ν

Date Code Key								
Year	2021	2022	2023	2024	2025	2026	2027	2028
Code		J	K	L	М	N	0	Р
		1	1			1	1	1
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug
Code	1	2	3	4	5	6	7	8

2032

υ

Dec

D



# Absolute Maximum Ratings – NPN (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	160	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Continuous Collector Current	Ic	200	mA

## Absolute Maximum Ratings – PNP (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-150	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Continuous Collector Current	Ι <sub>C</sub>	-200	mA

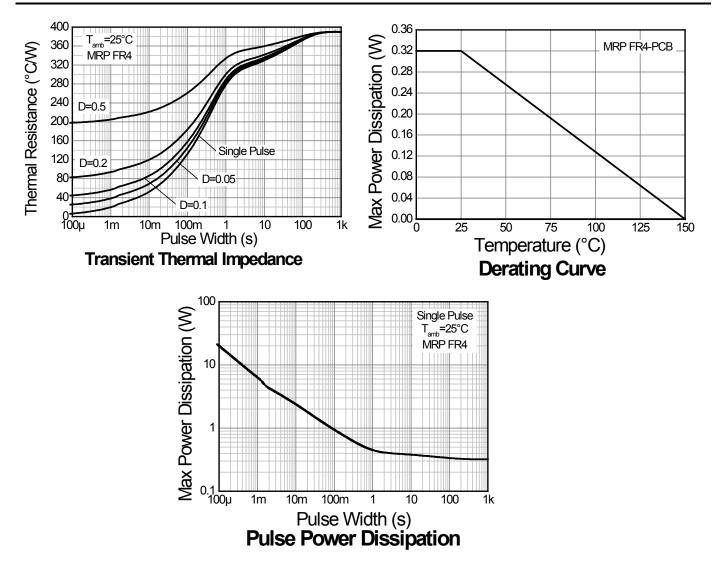
## Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	D	200	mW	
	(Note 6, 7)	P <sub>D</sub>	320		
Thermal Resistance, Junction to Ambient	(Note 5)	P	625		
	(Note 6, 7)	R <sub>θJA</sub>	390	°C/W	
Thermal Resistance, Junction to Case (Note 8)		R <sub>0JC</sub>	140		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

Notes: 5. For a device mounted on minimum recommended pad layout 1oz weight copper that is on a single-sided FR-4 PCB; device is measured under still air To a device included of minimum recommended pair conditions whilst operating in a steady-state.
Same as Note 5, except the device uses 2oz copper.
Maximum combined dissipation.
Thermal resistance from junction to the top of package.



#### Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)





#### Characteristic Symbol Min Max Unit Test Condition Тур **OFF CHARACTERISTICS** Collector-Base Breakdown Voltage $\mathsf{BV}_{\mathsf{CBO}}$ 180 V $I_{C} = 100 \mu A$ , $I_{E} = 0$ \_ \_\_\_\_ Collector-Emitter Breakdown Voltage (Note 9) 160 V **BV**CEO $I_{C} = 1mA$ , $I_{B} = 0$ 6 V $I_E = 10 \mu A$ , $I_C = 0$ Emitter-Base Breakdown Voltage **BV**<sub>EBO</sub> \_\_\_\_ \_\_\_\_ $V_{CB}$ = 120V, $I_{E}$ = 0 50 nA Collector-Base Cutoff Current I<sub>CBO</sub> 50 μA $V_{CB}$ = 120V, $I_E$ = 0, $T_A$ = +100°C **Base-Emitter Cutoff Current** 50 $V_{EB} = 4V, I_{C} = 0$ **I**EBO nA **ON CHARACTERISTICS (Note 9)** 80 $I_{C}$ = 1.0mA, $V_{CE}$ = 5.0V \_\_\_\_ DC Current Gain 80 250 $I_{C}$ = 10mA, $V_{CE}$ = 5.0V h<sub>FE</sub> \_\_\_\_ \_\_\_\_ 30 $I_{C}$ = 50mA, $V_{CE}$ = 5.0V 0.15 I<sub>C</sub> = 10mA, I<sub>B</sub> = 1.0mA V Collector-Emitter Saturation Voltage V<sub>CE(sat)</sub> 0.20 I<sub>C</sub> = 50mA, I<sub>B</sub> = 5.0mA $I_{C}$ = 10mA, $I_{B}$ = 1.0mA V **Base-Emitter Saturation Voltage** 1.0 V<sub>BE(sat)</sub> I<sub>C</sub> = 50mA, I<sub>B</sub> = 5.0mA SMALL SIGNAL CHARACTERISTICS pF Output Capacitance 6.0 Cobo $V_{CB}$ = 10V, f = 1.0MHz, I<sub>E</sub> = 0 \_\_\_\_ Small Signal Current Gain 50 250 $I_{C}$ = 1mA, $V_{CE}$ = 10V, f = 1.0MHz h<sub>fe</sub> \_\_\_\_ Current Gain-Bandwidth Product 100 300 MHz f⊤ \_\_\_\_ $I_{C}$ = 10mA, $V_{CE}$ = 10V, f = 100MHz

#### Electrical Characteristics – NPN (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

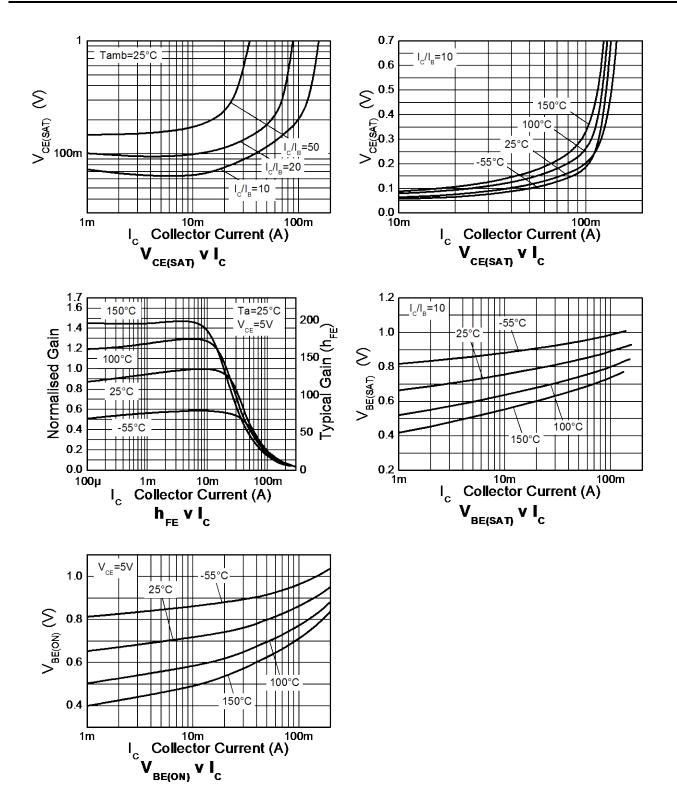
#### Electrical Characteristics – PNP (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS	ŀ			•	•	
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-160		—	V	$I_{\rm C} = -100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-150		—	V	I <sub>C</sub> = -1mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6		—	V	$I_{\rm E} = -10\mu A, I_{\rm C} = 0$
Collector-Base Cutoff Current		_		-50	nA	$V_{CB} = -120V, I_E = 0$
	I <sub>CBO</sub>	_		-50	μA	V <sub>CB</sub> = -120V, I <sub>E</sub> = 0, T <sub>A</sub> = +100°C
Base-Emitter Cutoff Current	I <sub>EBO</sub>	_	_	-50	nA	$V_{EB} = -4V, I_C = 0$
ON CHARACTERISTICS (Note 9)						
		50		_		I <sub>C</sub> = -1.0mA, V <sub>CE</sub> = -5.0V
DC Current Gain	h <sub>FE</sub>	60		240		$I_{C}$ = -10mA, $V_{CE}$ = -5.0V
		50				I <sub>C</sub> = -50mA, V <sub>CE</sub> = -5.0V
Collector Emitter Saturation Voltage			_	-0.20	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			-0.50		I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA
Dage Emitter Seturation Voltage	N/		_	-1.0	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>					I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>			6.0	pF	V <sub>CB</sub> = -10V, f = 1.0MHz, I <sub>E</sub> = 0
Small Signal Current Gain	h <sub>fe</sub>	40		260		I <sub>C</sub> = -1mA, V <sub>CE</sub> = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	f⊤	100		300	MHz	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -10V, f = 100MHz

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.

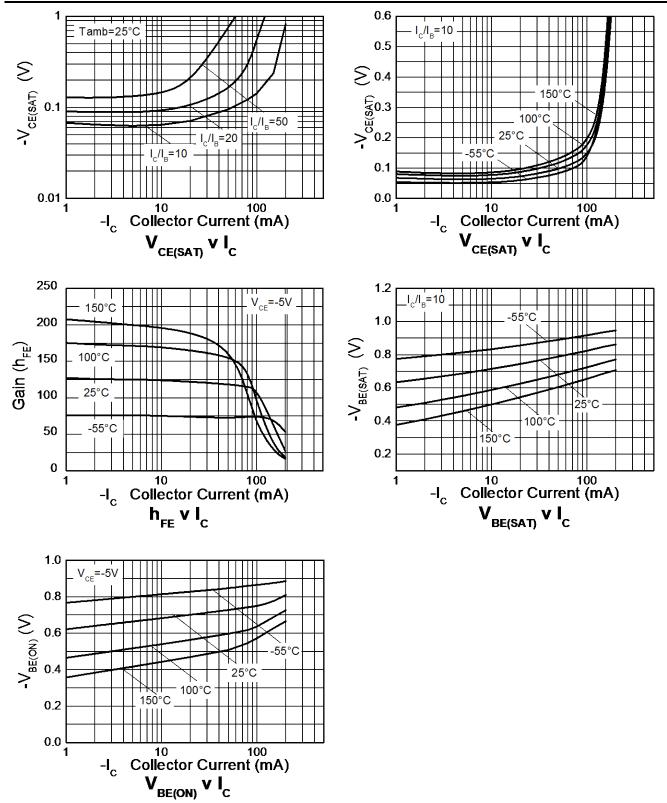


# Typical Electrical Characteristics – NPN (@ T<sub>A</sub> = +25°C, unless otherwise specified.)





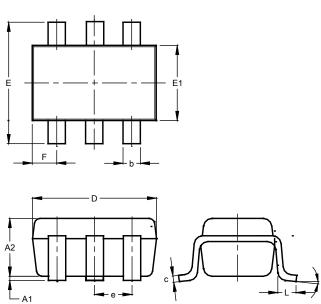
## Typical Electrical Characteristics – PNP 5401 Section (@ T<sub>A</sub> = +25°C, unless otherwise specified.)





## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

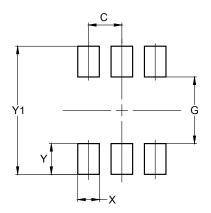


	80	17262					
Diss	SOT363						
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	1.00				
b	0.10	0.30	0.25				
С	0.10	0.22	0.11				
D	1.80	2.20	2.15				
E	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	0	).650 B	SC				
F	0.40	0.45	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All	All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500



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